



SOT-23 Plastic-Encapsulate Transistors

MMBT3906LT1 TRANSISTOR (PNP)

FEATURES

- As complementary type, the NPN transistor MMBT3904LT1 is Recommended
- Epitaxial planar die construction

MARKING: 2A



MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.2	A
P_C	Collector Dissipation	0.3	W
T_J, T_{stg}	Junction and Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -40\text{V}, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -10\text{mA}$	100	300	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	60		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$		-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$		-0.95	V
Transition frequency	f_T	$V_{CE} = -20\text{V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	250		MHz
Delay Time	t_d	$V_{CC} = -3.0\text{V}, V_{BE} = -0.5\text{V}$		35	nS
Rise Time	t_r	$I_C = -10\text{mA}, I_{B1} = -1.0\text{mA}$		35	nS
Storage Time	t_s	$V_{CC} = -3.0\text{V}, I_C = -10\text{mA}$		225	nS
Fall Time	t_f	$I_{B1} = I_{B2} = -1.0\text{mA}$		75	nS